



TM05G03HMI6

N+P-Channel Enhancement Mode Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

Product Summary

N Channel

$V_{DS} = 30V, I_D = 4.0A$
 $R_{DS(ON)} = 29m\Omega (typ.) @ V_{GS} = 10V$

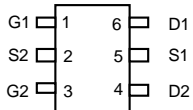
P Channel

$V_{DS} = -30V, I_D = -4.0A$
 $R_{DS(ON)} = 53m\Omega (typ.) @ V_{GS} = -10V$

100% UIS Tested
 100% R_g Tested

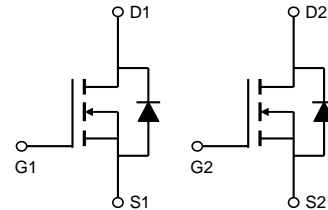
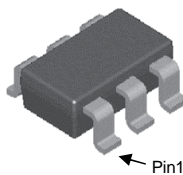


Top View



Marking: 4G03

MI6:SOT-23-6L



Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	4	-4.0	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	2	-2.5	A
I_{DM}	Pulsed Drain Current ²	20	-22	A
EAS	Single Pulse Avalanche Energy ³	72	79	mJ
I_{AS}	Avalanche Current	21	-21	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	1.5	2.08	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	50	$^\circ C/W$



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N-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}= \pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	$V_{GS}=10V, I_D=4A$	-	29	38	m Ω
		$V_{GS}=4.5V, I_D=3A$	-	45	65	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0MHz$	-	233	-	pF
C_{oss}	Output Capacitance		-	44	-	pF
C_{rss}	Reverse Transfer Capacitance		-	33	-	pF
Q_g	Total Gate Charge	$V_{DS}=15V, I_D=2A,$ $V_{GS}=10V$	-	3	-	nC
Q_{gs}	Gate-Source Charge		-	0.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	0.8	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V,$ $I_D=4A, R_{GEN}=3\Omega,$ $V_{GS}=10V$	-	4	-	ns
t_r	Turn-on Rise Time		-	2.1	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	15	-	ns
t_f	Turn-off Fall Time		-	3.2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	4.0	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=4A$	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$



P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -20V, V _{GS} =0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.5	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} = -4.5V, I _D = -3A	-	53	65	mΩ
		V _{GS} = -2.5V, I _D = -2A	-	75	93	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -10V, V _{GS} =0V, f=1.0MHz	-	393	-	pF
C _{oss}	Output Capacitance		-	47	-	pF
C _{rss}	Reverse Transfer Capacitance		-	38	-	pF
Q _g	Total Gate Charge	V _{DS} = -10V, I _D = -2A, V _{GS} = -4.5V	-	7.1	-	nC
Q _{gs}	Gate-Source Charge		-	1.2	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	1.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -10V, I _D = -3A, R _G =1Ω, V _{GEN} = -4.5V, R _L =1.2Ω	-	9	-	ns
t _r	Turn-on Rise Time		-	2.88	-	ns
t _{d(off)}	Turn-off Delay Time		-	22.3	-	ns
t _f	Turn-off Fall Time		-	3.9	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-4	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-12	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -3A	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



N-Channel Typical Characteristics

Figure 1: Output Characteristics

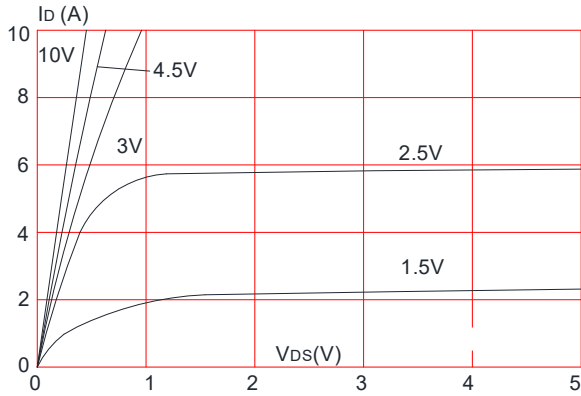


Figure 2: Typical Transfer Characteristics

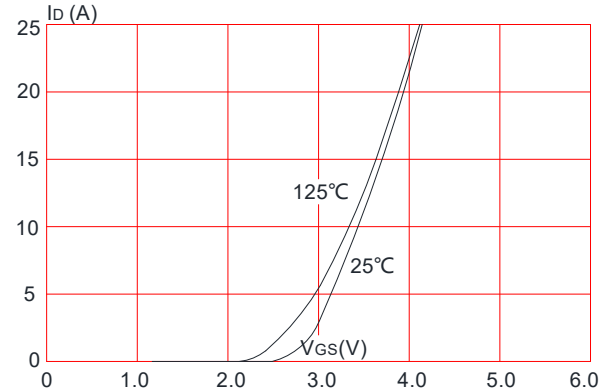


Figure 3: On-resistance vs. Drain Current

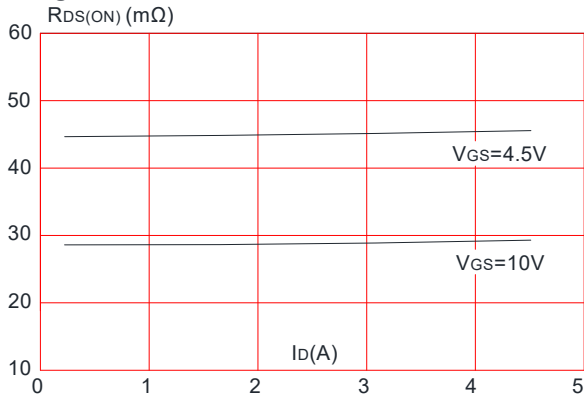


Figure 4: Body Diode Characteristics

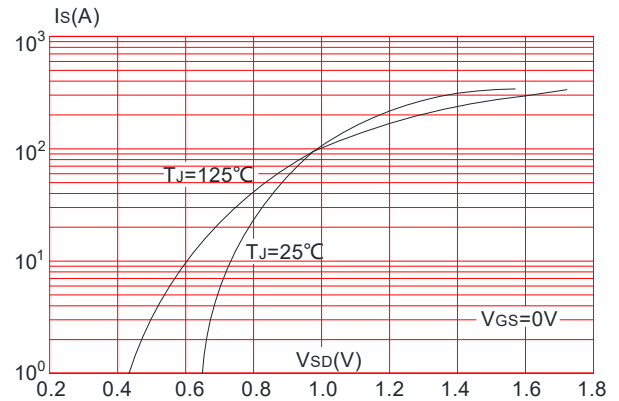


Figure 5: Gate Charge Characteristics

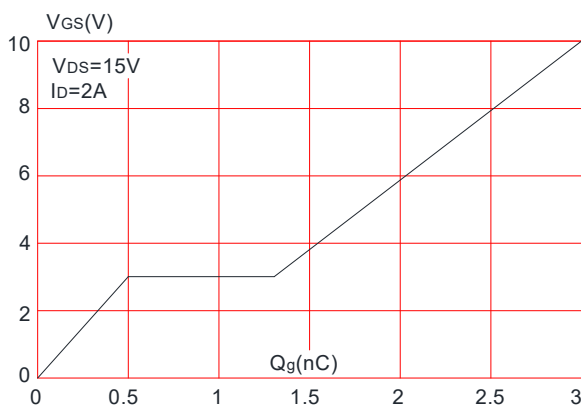
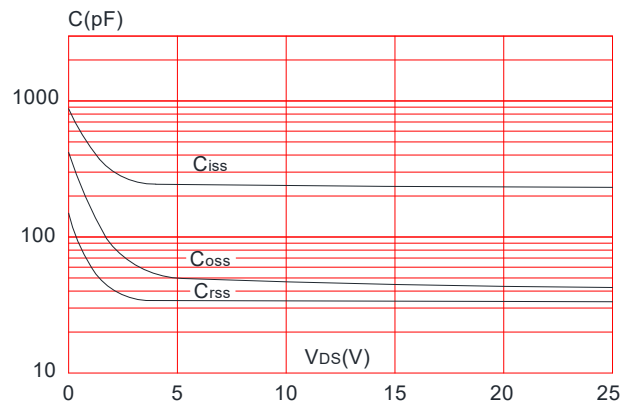


Figure 6: Capacitance Characteristics





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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

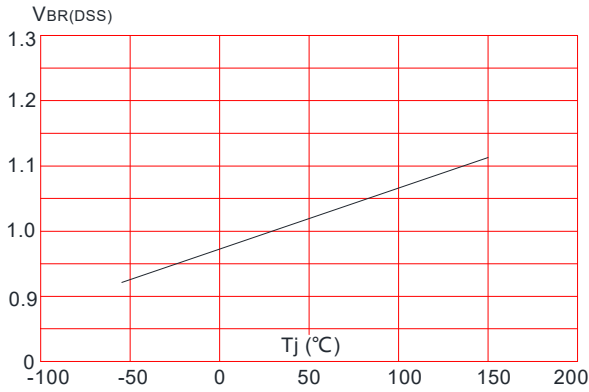


Figure 9: Maximum Safe Operating Area

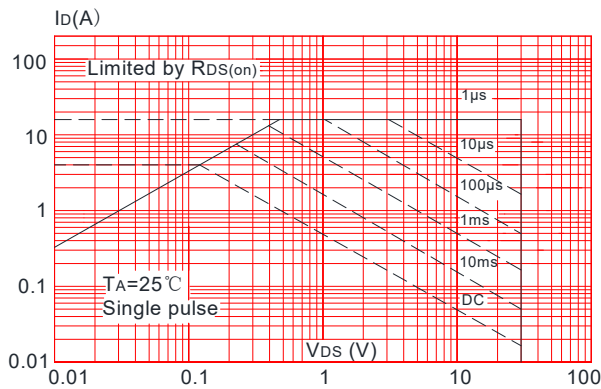


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

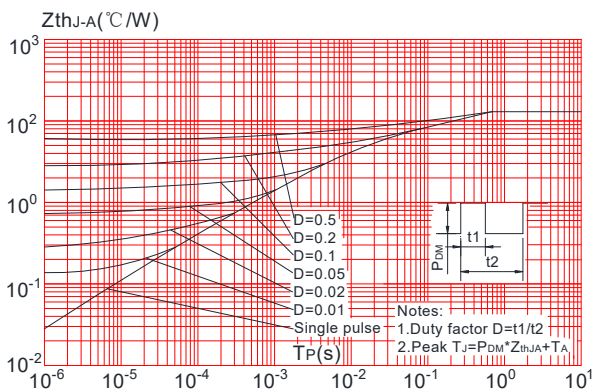


Figure 8: Normalized on Resistance vs. Junction Temperature

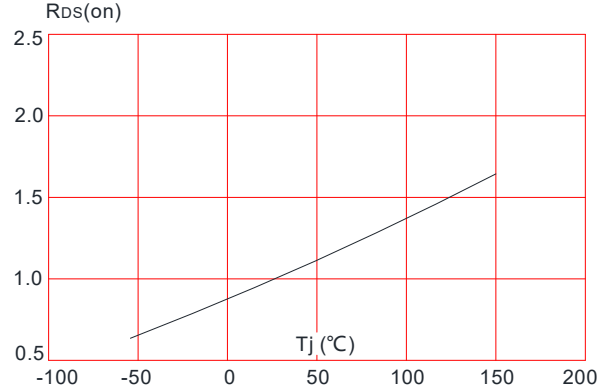
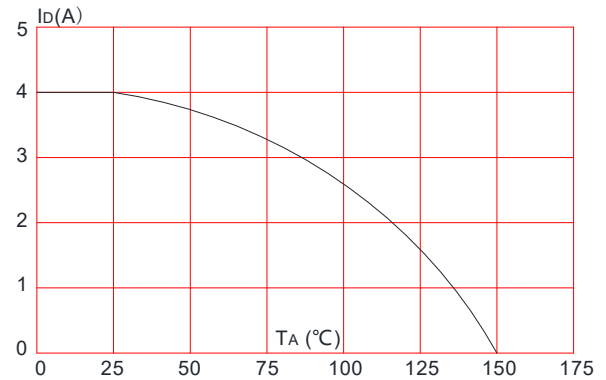


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature





P-Typical Characteristics

Fig 1: Output Characteristics

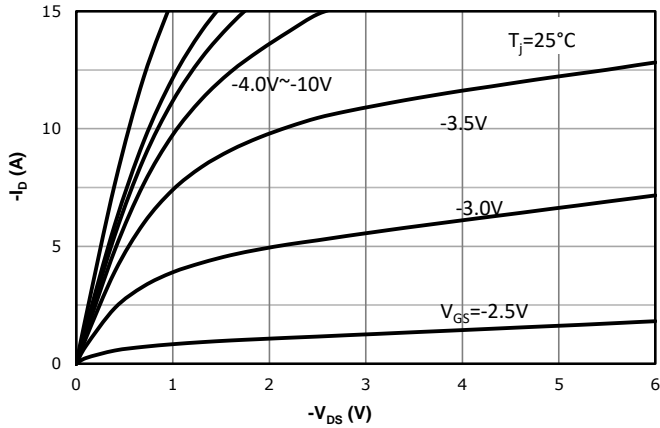


Fig 2: Transfer Characteristics

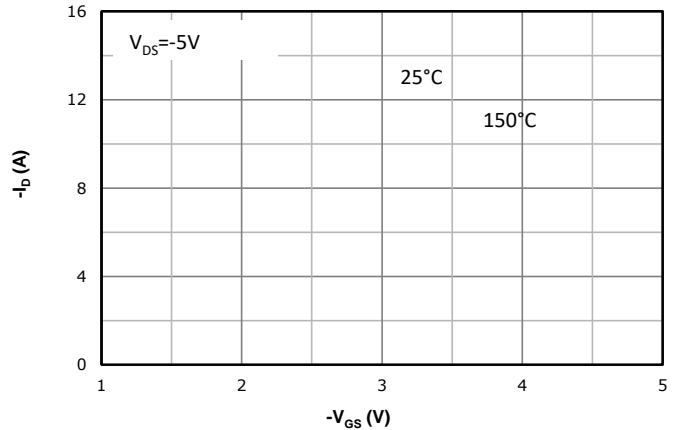


Fig 3: Rds(on) vs Drain Current and Gate Voltage

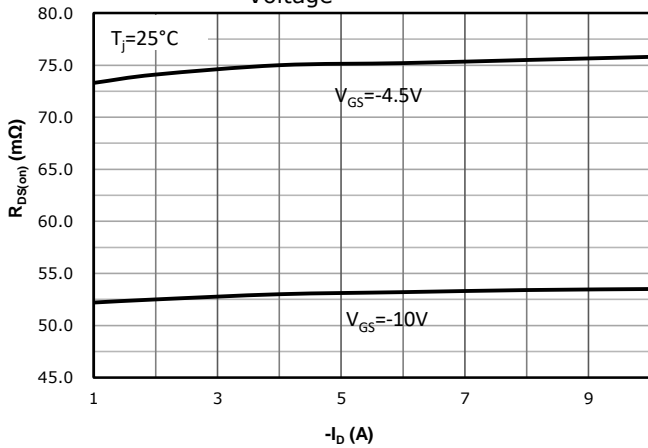


Fig 4: Rds(on) vs Gate Voltage

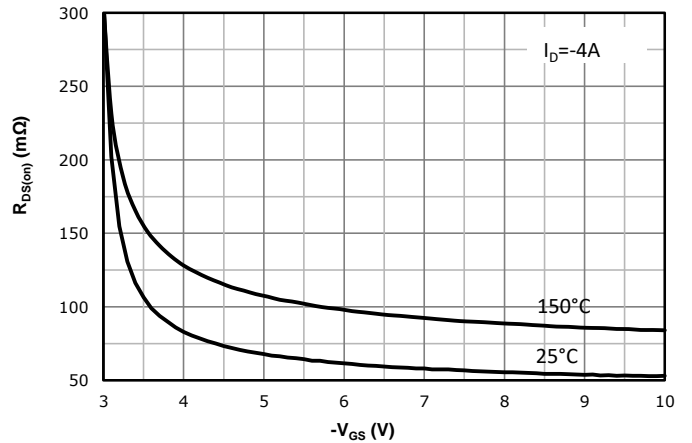


Fig 5: Rds(on) vs. Temperature

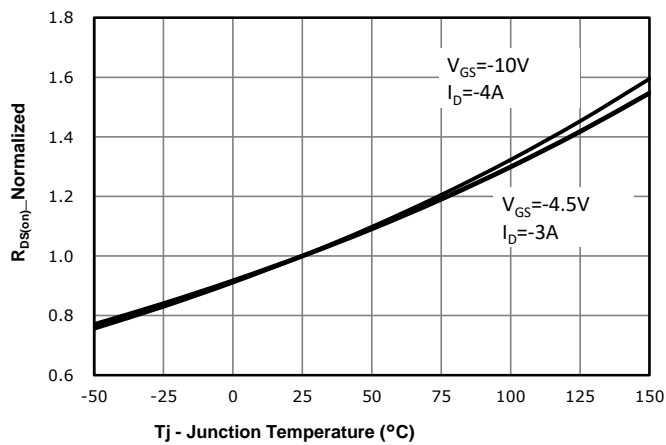
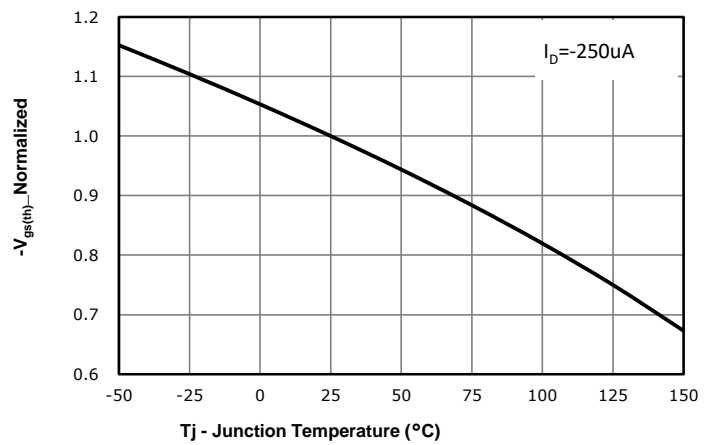


Fig 6: Vgs(th) vs. Temperature





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Fig 7: BVdss vs. Temperature

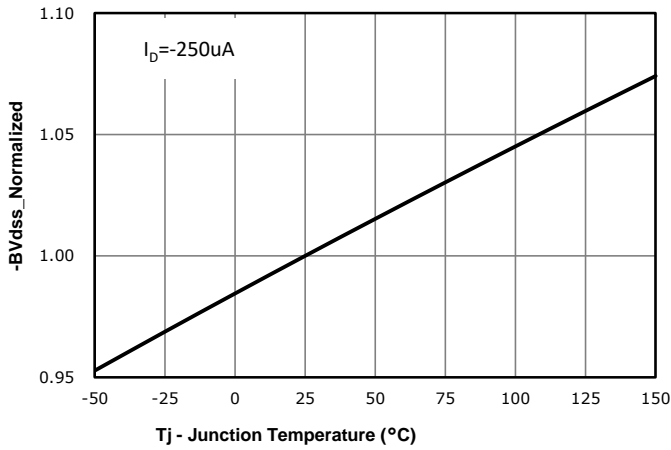


Fig 8: Body-diode Forward Characteristics

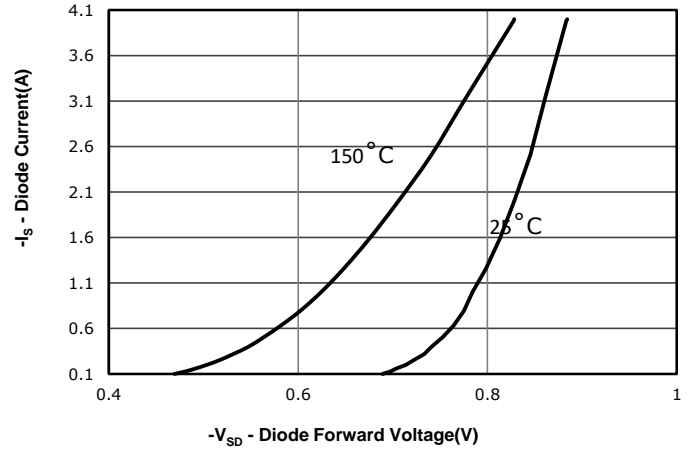


Fig 9: Gate Charge Characteristics

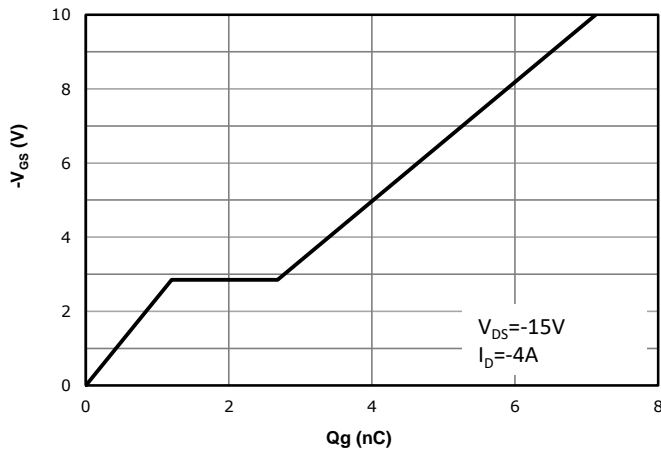


Fig 10: Capacitance Characteristics

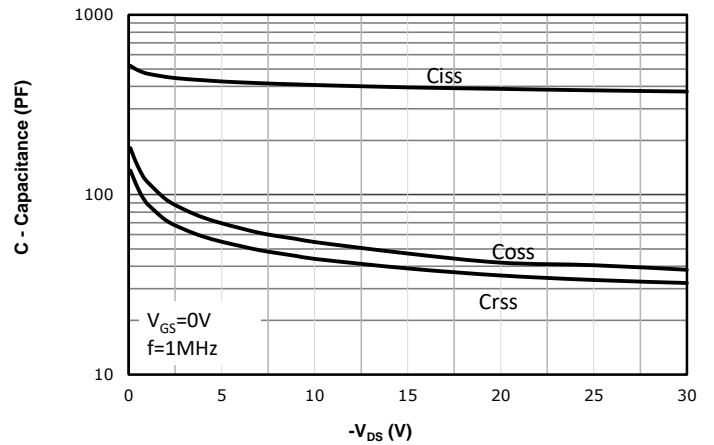


Fig 11: Drain Current Derating

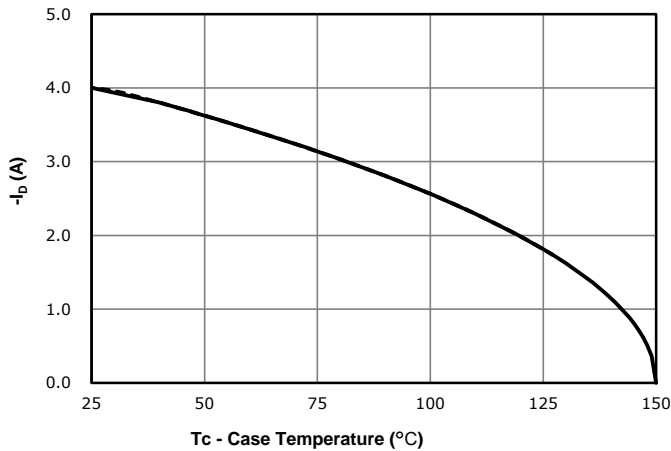
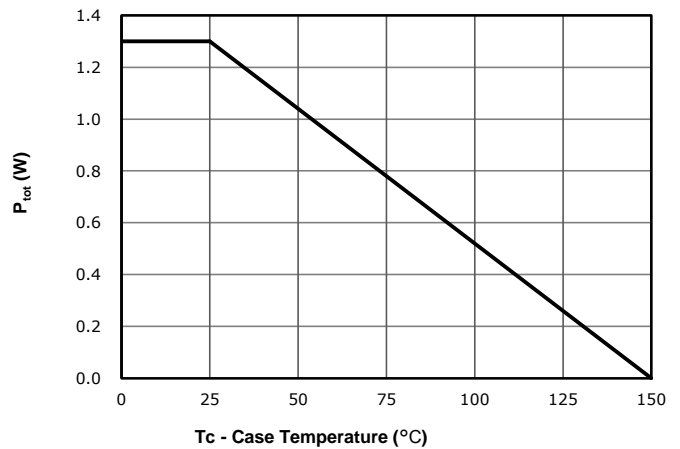


Fig 12: Power Dissipation





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Fig 13: Safe Operating Area

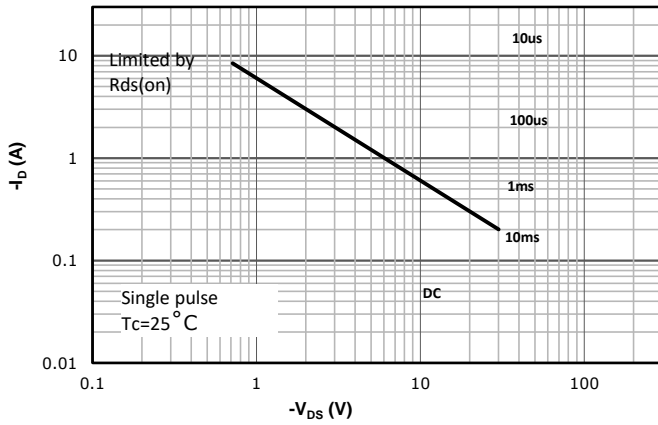
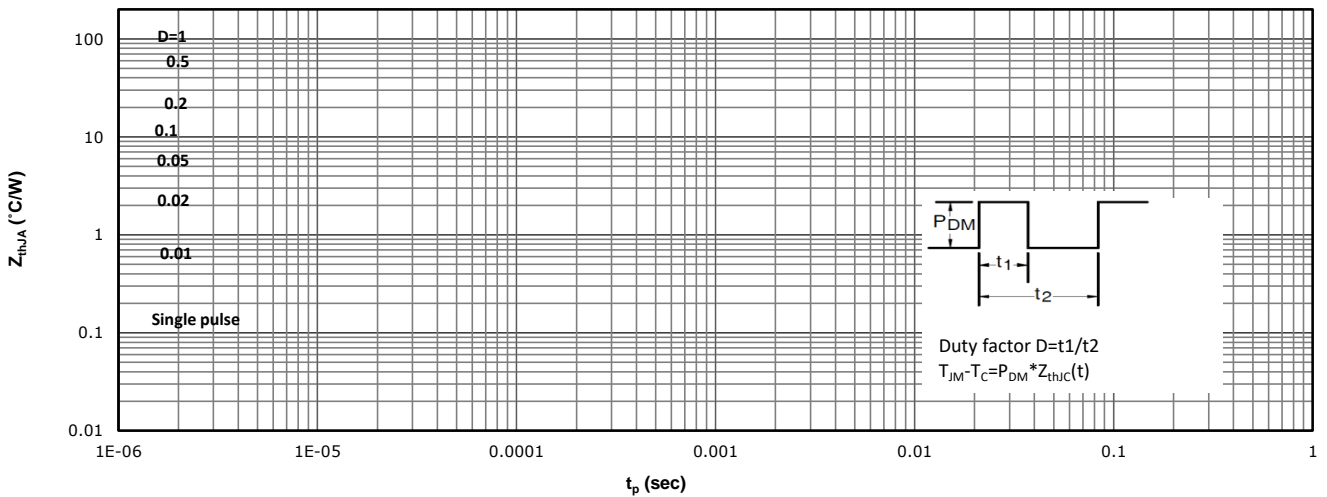
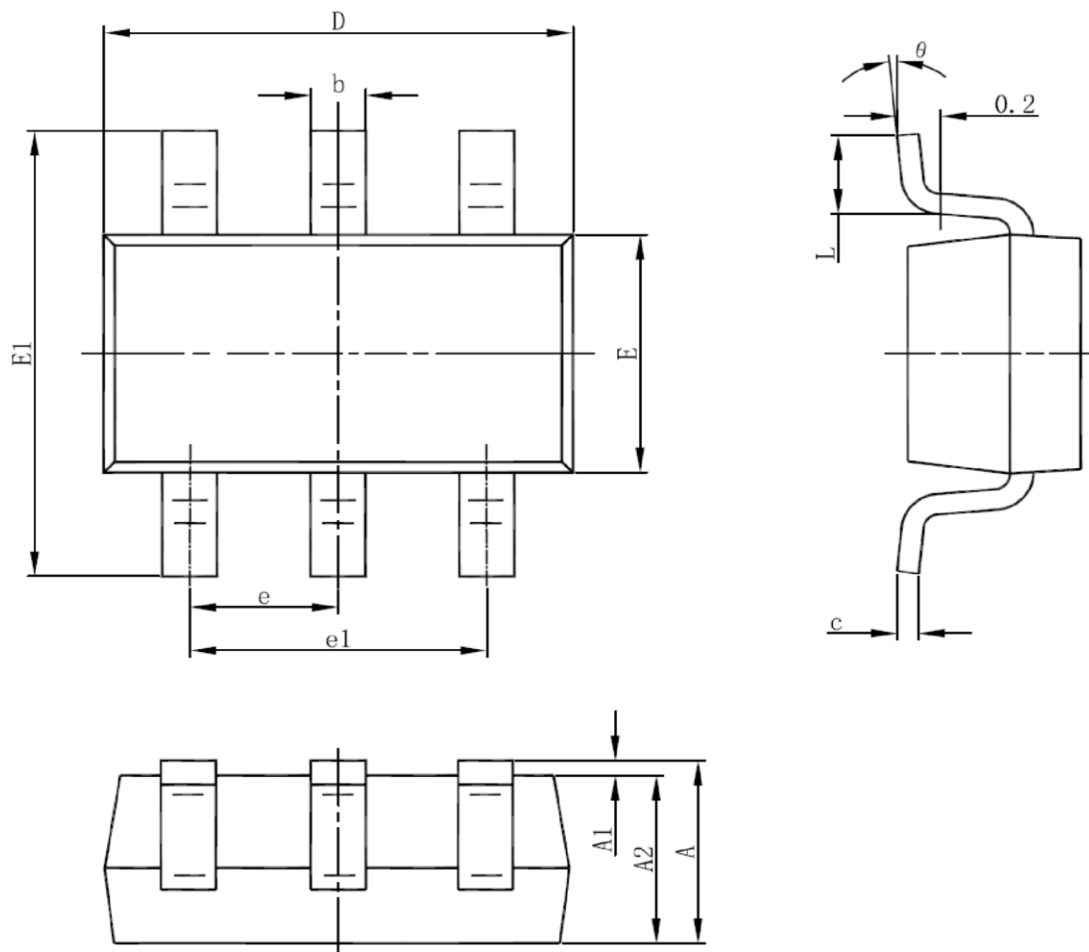


Fig 14: Max. Transient Thermal Impedance



Package Mechanical Data:SOT-23-6L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°